

17 - 24 GHz GaAs Power Amplifier/Driver MMIC

 4 Stage Monolithic Microwave Integrated Circuit (MMIC) Amplifier

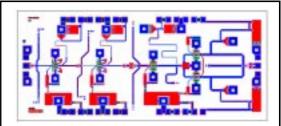
• Input/Output matched (incl. bond wires)

• Frequency range: 17 GHz to 24 GHz

• High Isolation > 50 dB

• Gain > 22 dB

• $P_{-1dB} > 23 \text{ dBm}, P_{sat} > 24 \text{ dBm}$



chip size: 4.2 mm x 1.8 mm

ESD: Electrical discharge sensitive device, observe handling precautions!

Description:

This 4 stage GaAs MMIC power amplifier is intended for use in radio link applications. It provides an output power of 23 dBm at 1 dB gain compression. The device is fabricated with a 0.18 micron Pseudomorphic InGaAs/AlGaAs/GaAs High Electron Mobility Transistor processing technology.

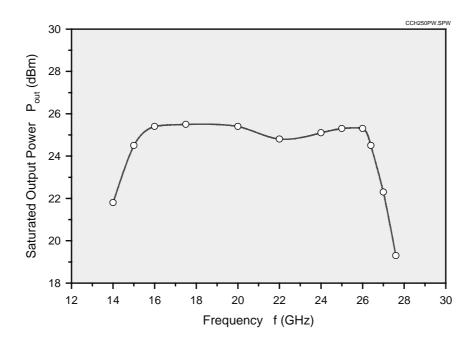
Туре	Ordering Code	Package
Chip T458B	tbd	Chip

Electrical Specifications: $(V_D = 5 - 6 \text{ V}, I_D = 300 \text{ mA})$

Parameter	Min	Тур	Max	Unit
Frequency Range	17		24	GHz
P _{-1dB}		23		dBm
Gain		22		dB
P _{sat}		24		dBm
PAE		15		%
Input Return Loss (incl. bond wire)		- 6		dB
Output Return Loss (incl. bond wire)		- 3		dB



Measured data: (on chip measurements)



Application Circuit:

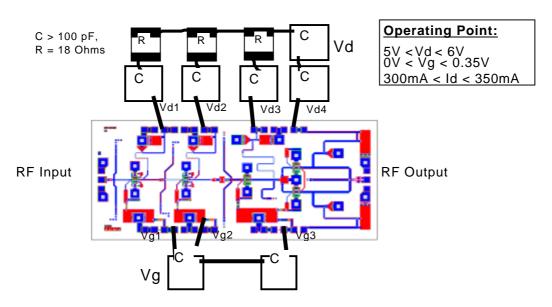
tbd.



Technology data:

Chip thickness	95µm	
Chip size	4,2 mm * 1,8 mm	
Bond pads	100 μm * 100 μm	
Bond pad material	Au (plated gold)	
Chip passivation	SiN (silicon nitride)	

Suggested measurement setup:



Recommendation of Bonding Conditions:

	Thermocompression Nailhead, without ultrasonic	Wedge Bonding	Bond Pull Test Mil 883, >2 g
Table Temp.	250°C	250°C	1: 2,5 g
Tool Temp.	180°C	150°C	2: 3,1 g
Scrub	100 Hz		3: 3,2 g
Bond Force	50 g	25 g	4: 3,0 g
Wire Diameter	25 μm	17 μm	5: 2,8 g



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